Surface electronic and structural properties of nanostructured titanium oxide grown by pulsed laser deposition

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1. Introduction

Titanium dioxide (TiO2) is a widely investigated material which has been successfully employed in many applications ranging from self-cleaning surfaces to electronics, energy and biotechnology [1,2]. For such applications the TiO2 surface electronic and structural properties are crucial: the presence of oxygen vacancies can affect the interaction with water in that it favours H2O dissociation and formation of hydroxyl groups [3,4], or alter the interaction with organic molecules [7].

Nanostructuring TiO2 can provide beneficial effects as for instance in photocatalytic properties or in superhydrophilic behaviour even without the need of UV irradiation, thus resulting in systems with enhanced performances [11–13]. Hence engineering the nanostructure and understanding how the surface electronic properties are related to the structure are of paramount importance in an applied technology context.

In this framework pulsed laser deposition (PLD) is a particularly attractive technique since it allows production of nanostructured films with tailored features. By ablating in the presence of a background gas, cluster formation is favoured and the kinetic energy of the deposited particles is reduced [11–13], thus allowing the synthesis of cluster-assembled films with an accurate control of morphology and structure [9,14,15]. Exploiting this approach, nanostructured TiO2 films showing interesting properties for biotechnology [8], photocatalytic [9] and photovoltaic [16] applications have been recently produced.

In the literature many studies devoted to the investigation of electronic and structural properties of TiO2 single crystalline surfaces [2] have been reported, while there is a much smaller number of studies of nanostructured TiO2 [17–26]. Even fewer reports describe explicitly the relationship [18,19,23–25] between different morphologies and corresponding surface electronic and structural properties.

In the present work, we aim to get a comprehensive picture of the surface properties of nanostructured TiO2 films obtained by PLD at...
room temperature in different oxidizing and inert background atmospheres and optionally annealed to tune their morphology and structure. These films consist of nano-aggregates (10–20 nm) ranging from amorphous to anatase and rutile phases assembled in compact or open morphologies which differ on the 10–100 nm scale [9].

Since the role of the surface properties such as structure, defects and stability, as well as surface contamination due to interaction with the atmosphere, is of particular interest for the above mentioned applications, we studied these surface properties under conditions close to those of applications. To avoid possible modifications due to cleaning procedures, films were measured ex situ without any further in situ treatment. In addition titanium metallic films were deposited to compare the effect of oxidation caused by exposure to the ambient atmosphere when the samples are extracted from the deposition chamber. Films characterized by a different morphology at the nanoscale have been investigated by means of ex-situ X-ray/UV photoelectron spectroscopy (XPS and UPS) at a synchrotron radiation facility. We monitored the presence of surface defects (i.e., oxygen vacancies) and of chemisorbed species (water molecules, organic contaminants and hydroxyl groups). The degree of crystalline order in the film surface was evaluated by near edge X-ray absorption fine structure (NEXAFS) and compared with complementary information coming from Raman spectroscopy. This cross linked analysis permits correlation of the structural properties arising from the nanoscale sizing with the corresponding surface electronic features and with the properties of the conduction and valence states close to the Fermi edge.

2. Experimental

Titanium oxide films were grown by PLD on Si(100) and Al substrates at room temperature exploiting UV laser pulses (duration ≈10–15 ns) from a KrF excimer laser (λ = 248 nm, 10 Hz repetition rate) focused on a Ti target (purity 99.99%) with an energy density (fluence) of about 3 J/cm². The deposition chamber was equipped with a multiple gas inlet system, allowing control of the gas composition and variation of the pressure from high vacuum (10⁻⁶ Pa base pressure) to atmospheric pressure. Films of ~200 nm thickness were grown with a target-to-substrate distance of 50 mm. Ar:O₂ — 4:1 mixture and pure Ar were employed as background gases during deposition and the total pressure was varied in the range between 10 and 60 Pa. The Ar:O₂ mixture was chosen to simulate synthetic air where Ar has been used instead of N₂ to avoid possible formation of nitrides. Post-deposition thermal treatment at 673 K was performed for 1 h in a muffle furnace in air. The temperature was chosen to induce structural ordering without inducing a phase transition from anatase to rutile. After the preparation, samples were...
either characterized immediately or stored in static vacuum until the measurements with the synchrotron light source could be performed.

SEM images were acquired with a Zeiss Supra 40 field emission scanning electron microscope. AFM images were collected in tapping mode with an Autoprobe CP II Research (Thermomicroscope) microscope in air using silicon tips with radius <10 nm (Nanosensors). Film density was evaluated by comparing deposited mass measured by a quartz microbalance with film thickness measured by cross sectional SEM. Visible Raman spectra were acquired with a Renishaw InVia spectrometer using the 514.5 nm wavelength of an argon ion laser. XPS, UPS and NEXAFS measurements were performed at the Material Science beamline at the Elettra synchrotron light source equipped with a plane grating monochromator [27] and a Specs Phoibos 150 mm hemispherical analyzer. No cleaning treatments were performed before acquiring normal emission photoelectron spectra at 650 eV photon energy with an overall spectral resolution of 0.5 eV. UPS data were collected at 50 eV and 200 eV photon energies with an overall energy resolution of 0.1 eV. Binding energies were referenced to the Au 4f core level emission spectra. The XPS spectra were normalized to the incoming photon flux and a standard curve fitting analysis (mixed Gaussian–Lorentzian line-shape) was performed to identify the different components. NEXAFS spectra were acquired in Auger electron yield mode at the Ti L2,3 and O K edges with a photon energy resolution of 0.1 eV. Calibration of the absorption spectra was carried out by measuring the photon energy using the Au 4f core lines excited with first order light. Curve fitting analysis was performed with WinspecTM software.

3. Results and discussion

3.1. Morphology and crystalline structure

Fig. 1a–d shows SEM images of films grown in Ar and Ar:O2 gases at different pressures (10–60 Pa). By increasing the Ar:O2 pressure we obtain films from compact and dense (Fig. 1a), to porous and columnar (at 30 Pa, Fig. 1c) morphology. At higher pressure the samples are porous with an extremely open morphology (60 Pa, Fig. 1b). Such porous systems with a high effective surface are composed of nanoparticles (size of about 10–20 nm) assembled in a hierarchical or disordered arrangement depending on the deposition pressure, as revealed by SEM and TEM images reported in previous works [9,16]. As a consequence the density decreases approximately from a maximum of ~2 g/cm³ to a minimum ~0.4 g/cm³ and the porosity correspondingly increases from 45% to more than 90%, as shown in previous work [9]. The surface roughness (root mean square roughness measured by AFM, images not shown) increases from 4.4 ± 0.2 nm to 13.2 ± 0.4 nm by increasing the deposition pressure from 10 Pa to 30 Pa. The effective surface evaluated from analysis of 1×1 μm² AFM images increases from 1.1 μm² at 10 Pa to 1.6 μm² at 60 Pa.

The film grown in a pure Ar background atmosphere at 30 Pa (see Fig. 1d) is even denser and smoother (2.5 ± 0.4 nm rms surface roughness) than the one grown at 10 Pa Ar:O2. When abating in an inert gas, only scattering of the ablated species takes place while no chemical reactions occur, leading to a different kinetic energy and temperature of the deposited species [28]. For the as-deposited samples, the Raman spectra presented in Fig. 2 are characterized by broad bands indicating a disordered titanium oxide structure for the film deposited at 10 Pa, while at 60 Pa Raman peaks typical of the crystalline anatase phase start to appear [29]. Although the most intense anatase peak at 144 cm⁻¹ is evident, other peaks belonging to the anatase phase at 399, 529 and 639 cm⁻¹ are not well defined and constitute an unresolved structure, indicating the coexistence of a disordered phase. Moreover, these wide bands could mask the two main peaks of rutile at 440 and 612 cm⁻¹, and thus the simultaneous presence of the rutile phase cannot be excluded a priori. Interestingly, also the as-deposited sample produced in a 30 Pa pure Ar atmosphere presents a Raman spectrum with broad bands typical of disordered TiO2. Since the film is 200 nm thick and the Raman cross section from disordered TiO2 is usually low, we can conclude that the oxidation, which occurs once the sample is removed from the growth chamber and exposed to air, may be favoured by the porous morphology and involves the film internal structure and not only the surface. None of the Raman spectra showed any quantum confinement effects (i.e. blue shift and broadening of the anatase peak at 144 cm⁻¹) which generally start to become visible for particle size below ~10 nm [30].

For all samples thermal treatment increases the crystalline order [9] while the morphology and the surface roughness are not significantly modified (see Fig. 1E and F). Nanoparticles constituting the nanostructured assembly increase their crystalline order without coalescing or growing in size. This is also supported by XRD measurements, reported in ref. [9], showing the presence of ordered grains with typical size changing from about 20 nm to 10 nm by increasing the pressure from 10 to 100 Pa. From the Raman spectra reported in Fig. 2, the main crystalline phase of the annealed samples is still anatase, identified by the peak at 144 cm⁻¹. Other peaks typical for anatase at 399, 529 and 639 cm⁻¹ are still not completely resolved and for samples grown at higher pressures (≥30 Pa), features at 447 and 612 cm⁻¹ appear, which indicate also the presence of the rutile phase [31].

3.2. Surface composition and electronic properties

3.2.1. Core level photoemission spectra

Selected Ti 2p, O Is and C Is core level XPS spectra are reported in Fig. 3 (see Supplementary Information for the complete set of spectra as well as the curve fitting analysis). All the investigated samples show the same Ti 2p spectra (see Fig. 3(a)), characterized by spin-orbit (1/2, 3/2) Ti³⁺ doublet components at 458.8 eV and 464.4 eV binding energy [2,18,32–35]. No Ti²⁺ shoulder at lower binding energy on the Ti 2p₁/₂ peak was detected, suggesting that all samples have a stoichiometric surface [33]. In the O Is spectra (see Fig. 3(b)) three contributions can be discerned for all
samples; one at \(-530.4\) eV binding energy due to the \(O^{2-}\) oxygen species of titanium dioxide. [33] one at \(-532.1\) eV assigned to (Ti bonded) \(OH^-\) hydroxyl oxygen and/or to C–O and O–C=O species coming from organic contaminants (the signal of hydroxyl groups cannot be distinguished from that of C–O and O–C=O species since they have similar binding energies)[36,37], while the one at \(-533\) eV may be due to adsorbed water molecules or to ester oxygen in a carboxyl group [33,37]. The main observable trend (see Table 1) among the as-deposited samples is an increase of organic contamination/hydroxyl oxygen and water uptake with increasing Ar:O\(_2\) pressure during deposition. This behaviour can be attributed not only to the higher surface area but also to a higher surface reactivity, as discussed in Section 3.3.

### Table 1

<table>
<thead>
<tr>
<th>TiO(_2) film deposited in</th>
<th>O(_{1s}) signal at (530.4) eV (%)</th>
<th>(Ti)–O–H; C–O; O–C=O (%)</th>
<th>(H_2O_{ads}; O=C=O) (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>As deposited</td>
<td>Annealed</td>
<td>As deposited</td>
<td>Annealed</td>
</tr>
<tr>
<td>10 Pa Ar:O(_2)</td>
<td>80 ± 1</td>
<td>80 ± 1</td>
<td>20 ± 1</td>
</tr>
<tr>
<td>30 Pa Ar:O(_2)</td>
<td>70 ± 3</td>
<td>70 ± 1</td>
<td>25 ± 2</td>
</tr>
<tr>
<td>60 Pa Ar:O(_2)</td>
<td>62 ± 1</td>
<td>63 ± 1</td>
<td>32 ± 1</td>
</tr>
<tr>
<td>30 Pa Ar</td>
<td>66 ± 1</td>
<td>74 ± 1</td>
<td>30 ± 1</td>
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Annealing does not modify the O\(_{1s}\) signals of the samples synthesized in Ar:O\(_2\) atmosphere. On the contrary, the contamination and \(OH^-\) signal of the sample synthesized in pure Ar atmosphere decreases after thermal treatment, probably related to the high reactivity of the metallic surface to oxygen, water and organic contaminants by air exposure, resulting in a larger amount of chemisorbed organic contaminants/OH\(^-\) groups.

At the same time, C\(_{1s}\) spectra (see Fig. 3(c)) can be fitted with three contributions at 284.6 eV, 286.2 eV and 288.2 eV binding energy and assigned to C–C/C–H, C–O and O–C=O groups [37]. The C\(_{1s}\) signals (see Table 2) increase with the pressure during deposition in both the as-deposited and the annealed samples, while at a given pressure the annealing treatment reduces the intensity of the carbon signal. For the sample deposited in Ar atmosphere, the C\(_{1s}\) intensity is slightly reduced compared to the sample deposited in Ar:O\(_2\) (at the same pressure) but higher compared to the one deposited in 10 Pa Ar: O\(_2\). Although it is not possible solely from the O\(_{1s}\) spectra to distinguish between OH groups bound to Ti and contaminant species, the ratio between the intensities of O\(_{1s}\) signal due to contaminants and OH groups (532.1 eV) and the sum of the oxygen-bonded C\(_{1s}\) components (286.2 eV and 288.2 eV), reported in Fig. 4, can give some hints about the OH groups present on the surface. This ratio increases a) with the deposition pressure and b) upon annealing for samples deposited in 30 and 60 Pa of Ar:O\(_2\) atmosphere. This behaviour may be explained by partial removal of C-containing contaminants and substitution with hydroxyl groups bonded to Ti surface after annealing [38]. Moreover, the sample synthesized in 30 Pa pure Ar presents a higher intensity ratio compared to samples grown in 10 Pa and 30 Pa Ar:O\(_2\) atmosphere, in agreement with the general observation that a partially oxidized Ti surface shows enhanced reactivity towards OH groups.

#### 3.2.2 Valence band photoemission spectra

Fig. 5(a) shows valence band photoemission spectra before and after the annealing procedure. At a photon energy of \(h\nu = 50\) eV the photoelectron escape depth is nearly 4\(\AA\) [39] and the spectra are therefore very sensitive to the electronic properties of the topmost surface layer. In agreement with previous studies [2,18,40], we assign the intense features located between 3.5 eV and 10 eV binding energy to O 2p–Ti 3d hybridized states. These two overlapping features correspond to different O 2p–Ti 3d hybridizations: the feature at 7 eV...
contains a higher Ti 3d contribution while the 5 eV feature has mainly O 2p character [40].

All the as-deposited samples grown in Ar:O2 atmospheres show a broad signal around 10.5 eV, the intensity of which scales with the deposition pressure. The sample grown at 30 Pa in pure Ar presents instead a much more intense feature, which has a completely different shape and is shifted to higher binding energy by nearly 0.5 eV. According to the literature, the 3σ orbital of OH is responsible for a VB spectral feature at a binding energy of ~10.8 eV [41] and organic contaminants can introduce an extra feature at ~11 eV [42]. In agreement with the analysis of the C 1s and O 1s core level spectra reported above, this difference confirms that the oxidation process, occurring exclusively in air for the sample grown in pure Ar, leads to a higher amount of organic contaminants and/or of hydroxyl groups. After annealing, the intensity of the feature at ~11 eV disappears in this sample, indicating desorption of organic contaminants bonded to the surface. The intensity increase of the ~10.5 eV binding energy feature with Ar:O2 pressure is in agreement with the intensity enhancement of the O 1s component (OH−/organic contaminants) in the XPS spectra.

In the as-deposited samples we observe the presence of a feature at ~1 eV below EF (see Fig. 5(b)) generally attributed to substoichiometric Ti3+ ions [2,43]. The nature of this reduced state is still controversial since both Ti interstitials and oxygen vacancies give rise to spectral intensity at ~1 eV binding energy [3,44]. Interestingly, we observed that in our case the presence of the defect state is induced by irradiation (see Fig. 5(c)) since the defect state appears after irradiating the same region for some minutes with a flux of about 1013 photons s−1 cm−2. This defect-induced effect is not observed in the Ti 2p core levels, probably because of the different photon flux (30–40 times lower) and the lower surface sensitivity when using a photon energy equal to 650 eV. Since the peak at ~1 eV is radiation induced, we believe that it is mainly due to oxygen vacancies and not to Ti interstitials. Vacancies may form by local excitation, local heating and irradiation by secondary electrons [45], which cause oxygen desorption [46] and/or removal of less stably bonded hydroxyl groups [47]. In annealed samples the surface seems to be more stable and defect-induced state forms only for the film grown at the highest pressure (60 Pa in Ar:O2) (see Fig. 5(b)).

3.2.3. NEXAFS analysis of titanium and oxygen edges

The local symmetry and the electronic environment of the titanium oxide surface have been investigated by X-ray absorption spectroscopy at the Ti L2,3 and O K-edges as shown in Fig. 6. Typically, the Ti L2,3 absorption spectra of TiO2 present four main peaks related to transitions from the Ti 2p core levels to the εg and εs orbitals which are affected by the oxygen ligands’ crystal field and hence by the different ligand configurations and local distortions [2].

In particular the εg states possess a large degree of hybridization and are very sensitive to the Ti atom local environment: sharp peaks occur in crystalline samples and the L1−εg band is further split into two sub-bands (Fig. 6c); more precisely in anatase the lower photon energy component of the L1−εg peak is more intense than the higher photon energy one, while the opposite is true in rutile [22]. Broader εg peaks occur in disordered materials (see Fig. 6(a)) (in our case, in samples with smaller grain size) and are attributed to distortions and random variations of bond angles and lengths.

Correspondingly the O K-edge absorption spectrum shows two main features at ~531 eV and ~534 eV (marked E and F in Fig. 6(b) and (d)). These peaks are due to excitations from O 1s levels to the εg and εs orbitals of TiO2: the unresolved structures at higher photon energy are due to transitions to antibonding bands derived from the covalent mixing of O 2p and Ti 4sp states [48]. The energy difference between the εg and εs features (E–F) at the O K-edge spectra is commonly used as an estimate of the crystal field splitting strength and amounts to ~3.0 eV in rutile and to 2.8 eV in anatase whereas it is reduced to 2.3 eV in disordered samples [22]. The crystal field splitting of the O K-edge bands reported in Fig. 6 increases from ~1.8 eV (as-deposited samples) to 2.5 eV (annealed samples). This splitting in the as-deposited sample is then lower than that observed for TiO2 aerogels [22] (2.3 eV) and this may be due to higher disorder in the coordination of the oxygen ligands and to a weaker Ti 3d−O 2p hybridization [49]. In the case of annealed samples, this splitting is lower compared to the single crystal structure but higher than for the aerogel sample.
The Ti \(L_{2,3}\) edge NEXAFS spectra (see Fig. 6(a) and (c)) give a more detailed knowledge and reveal further differences on the samples. The results of the curve fitting analysis of the Ti \(L_{2,3}\) edge NEXAFS spectra are presented in Table 3. The spectra were fitted by mixed Gaussian/Lorentzian peaks: (i) two pre-edge features at \(h\nu = 456.5\) eV and \(h\nu = 457.5\) eV, (ii) one \(t_{2g}^*\) peak at \(h\nu \sim 458\) eV and (iii) two peaks \((e_{g}^* B_1, e_{g}^* B_2)\) to reproduce the \(e_{g}^*\) band; the corresponding peaks at the \(L_2\) edge were fitted in an analogous fashion. The results (see Table 3) clearly point to a transition to a crystalline phase after annealing at 673 K for some samples, namely the samples deposited in 10 Pa Ar:O\(_2\) and 30 Pa Ar atmosphere. For these samples, the \(B_1\) peak becomes narrower: a difference of 0.3 eV (10 Pa Ar:O\(_2\)) and 0.4 eV (30 Pa Ar) after annealing. Concurrently the \(t_{2g}^*\) and \(e_{g}^* B_2\) peaks’ intensities increase (by \(-30\%\)) after annealing at 673 K, while the \(e_{g}^* B_1\) peak decreases. In the 60 Pa sample instead, differences before and after annealing are almost absent, while the behaviour of the 30 Pa Ar:O\(_2\) sample is intermediate between the 10 Pa and 60 Pa suggesting a partial phase transition.

Since the \(t_{2g}^*\) and \(e_{g}^* B_2\) peaks are related to the crystalline order while the \(e_{g}^* B_1\) peak is more related to the remaining disordered phase [50], the intensity enhancement of the former (in 10 Pa Ar:O\(_2\) and 30 Pa Ar) supports local ordering of TiO\(_2\) at the surface after annealing. In particular, the shape of the Ti \(L_3-e_{g}^* B_1\) peak confirms that the local surface symmetry and ligand coordination are typical of the anatase phase in the annealed samples, while the samples produced in 30 and 60 Pa Ar:O\(_2\) are less ordered.

Further differences emerge comparing samples deposited at different pressures: with increasing pressure during deposition, the relative intensity of the \(L_3-t_{2g}^*\)-related feature decreases compared to the relative intensity of the \(L_3-e_{g}^* B_1\) peak, pointing to lower local symmetry or higher concentration of defects. This agrees also with the observed lower \(L_3-e_{g}^* B_1\) peak splitting and generally broader peaks for higher pressures during film growth. This trend is more marked in the annealed samples, indicating a greater difference in local surface order.

### 3.3. Discussion

With the help of O 1s and VB photoemission spectra as well as NEXAFS spectra, we have highlighted differences depending on the pressure during deposition, the background gas composition, and the temperature treatment; considering all the presented experimental
data, we can draw a comprehensive picture of the relation between surface electronic and structural properties and the nanostructure of TiO₂ films grown by PLD.

A comparison with literature results shows that as-deposited samples present NEXAFS features similar to amorphous TiO₂ or to titania aerogels. Comparison with Raman data provides complementary information compared to NEXAFS since it probes the internal film structure and it is sensitive to the structural order on a longer range. The Raman signal from small crystalline domains of the anatase phase increases for samples produced in a high background pressure, while on the surface the bond angles and lengths are very disordered, as evidenced by NEXAFS. As expected, after annealing the local order at the surface is increased, in particular for denser films (i.e. films deposited in lower background pressures), even though the NEXAFS peaks are broader than for single crystalline surfaces, indicating a residual variation in local bond angles and lengths [22]. The higher surface local ordering is related to easier nano-crystalline grain formation in compact films, as supported also by XRD data [9]. The Raman spectrum of annealed films is dominated by resolved anatase-type peaks and, for samples produced in high background pressures, there is also a weak rutile signal. This suggests the presence of small rutile grains buried below a surface layer of atoms with a weak anatase-type coordination, as evidenced by NEXAFS.

We observe that defects are more easily induced on as-deposited samples than on annealed surfaces, and that even with less marked differences, samples deposited at lower pressures show a higher stability towards photon induced defects. The surface stability is improved in surfaces with a higher structural order as shown by NEXAFS.

The surface structure has a leading role in the interaction with OH and contaminants. Of course also the film morphology has a profound effect on the surface properties but the increase in the effective surface area alone cannot account for the observed variations of OH/contaminants. In fact, in as-deposited samples a 1.5-fold increase of surface area (obtained from analysis of the AFM images) is observed when changing from 10 to 60 Pa deposition pressure, and this leads to an approximately 2-fold rise of the intensity due to organic contaminants/OH⁻ in the XPS O 1s spectra (normalized to the Ti 2p intensity), and an even higher increase of the main C 1s signal. As expected, samples deposited in a higher background pressure have a larger surface area available to host or trap molecules; however, the dissociation of water and organic molecules is favoured at oxygen vacancies [32,51,52] and some studies point to the fact that, compared to single crystals, nanostructured surfaces include a higher amount of native defects, which are saturated through air exposure [10,19,53]. The importance of native defects is underlined by the samples deposited in 30 Pa of pure Ar. In this case, despite its more compact and smoother morphology, the surface is certainly more defective as suggested by the higher C–O/OH¯ contribution in the O 1s and C 1s core levels, and by the intense peak at ~11 eV in the VB photoemission spectrum, indicating that it is more hydroxylated. This implies that the surface structure (i.e., the presence of defects) determines the density of contaminants, more than the morphology itself. The annealing procedure strongly influences the surface reactivity leading to an increase in grafted hydroxyl radicals. This mechanism, explained as a removal of organic contaminants (probably saturating defects sites) and replacement with OH groups, may influence the wettability properties required for superhydrophilicity [38].

4. Conclusions

Exploiting synchrotron-based spectroscopy and microscopy techniques, we investigated the surface structure of TiO₂ thin films characterized by varying morphology and structural order at the nanoscale. The morphology (density and roughness of the sample), which can be tuned in the PLD process by changing the deposition parameters, is not affected by annealing, while structural and surface electronic properties are significantly modified. Moreover, when the sample is more compact and smooth, annealing enhances the local ordering and the stability under photon beam irradiation, as shown by the lower density of photon-induced defect states in the valence band spectra.

This complete characterization of the morphological, electronic and structural properties allows us to understand what governs the surface properties of TiO₂ thin films. The nanoscale morphology and porosity together with structure, and the presence of surface defects determine the amount and type of hydroxyl group and/or organic contamination. This may in turn significantly affect surface properties relevant for a wide range of applications in which surface mediated processes have a key role, such as photocatalytic activity, wettability properties, and interaction with organic and biological molecules (e.g. dyes, polymers and proteins) that are of technological interest for developing materials and systems such as self-cleaning [9] and antifog surfaces, dye sensitized or hybrid photovoltaic devices [16] and biosensors [8].

Acknowledgements


Appendix A. Supplementary data

Supplementary data to this article can be found online at doi:10.1016/j.susc.2010.10.039.

References


